

## Product Summary

BV <sub>bss</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>c</sub> = +25°C
40V	15mΩ @ V <sub>GS</sub> = 10V	42A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Backlighting
- Power-management functions
- DC-DC converters

## Features and Benefits

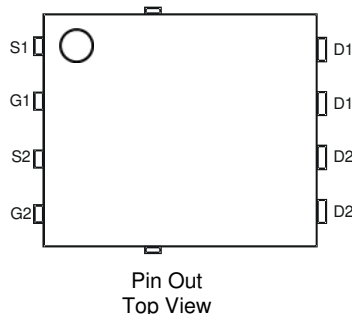
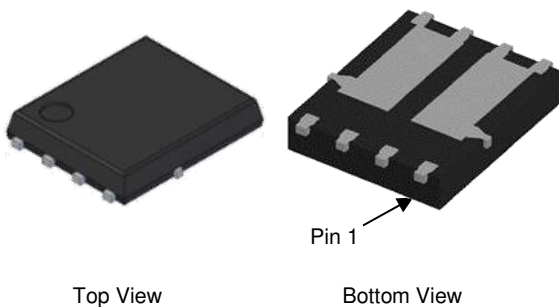
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**  
<https://www.diodes.com/quality/product-definitions/>
- **An automotive-compliant part is available under separate datasheet (DMTH4011SPDQ)**

## Mechanical Data

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)

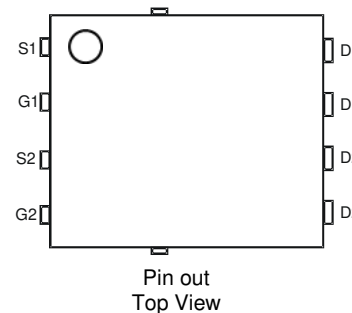
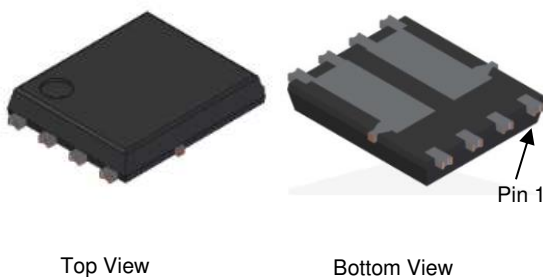
Site 1:

PowerDI5060-8 (Type C)



Site 2:

PowerDI5060-8/SWP (Type UXD)

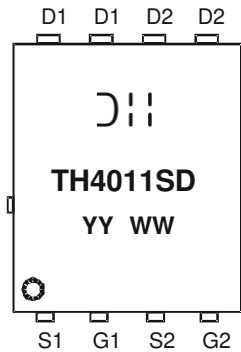


- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

**Ordering Information** (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH4011SPD-13	PowerDI5060-8 (Type C)	2,500	Tape & Reel
	PowerDI5060-8/SWP (Type UXD)	2,500	Tape & Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**


☐|| = Manufacturer's Marking  
 TH4011SD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 23 = 2023)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	I <sub>D</sub>	T <sub>C</sub> = +25°C	42
		T <sub>C</sub> = +100°C	29.7
Continuous Drain Current (Note 6)	I <sub>D</sub>	T <sub>A</sub> = +25°C	11.1
		T <sub>A</sub> = +100°C	7.8
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	60	A
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	3.3	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	60	A
Avalanche Current, L = 0.3mH	I <sub>AS</sub>	11.9	A
Avalanche Energy, L = 0.3mH	E <sub>AS</sub>	21.4	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	57	°C/W
Total Power Dissipation (Note 5)	P <sub>D</sub>	37.5	W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

Notes: 5. Thermal resistance from junction to soldering point (on the exposed drain pad).  
 6. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	11.6	15	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	805	—	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	208	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	15	—	pF	
Gate Resistance	R <sub>g</sub>	—	2.76	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	10.6	—	nC	V <sub>DS</sub> = 20V, I <sub>D</sub> = 20A V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	2.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	2.7	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.1	—	ns	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V R <sub>g</sub> = 1.6Ω, I <sub>D</sub> = 20A
Turn-On Rise Time	t <sub>R</sub>	—	3.8	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	8.6	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	1.9	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	10.2	—	ns	I <sub>F</sub> = 15A, di/dt = 400A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	9.6	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

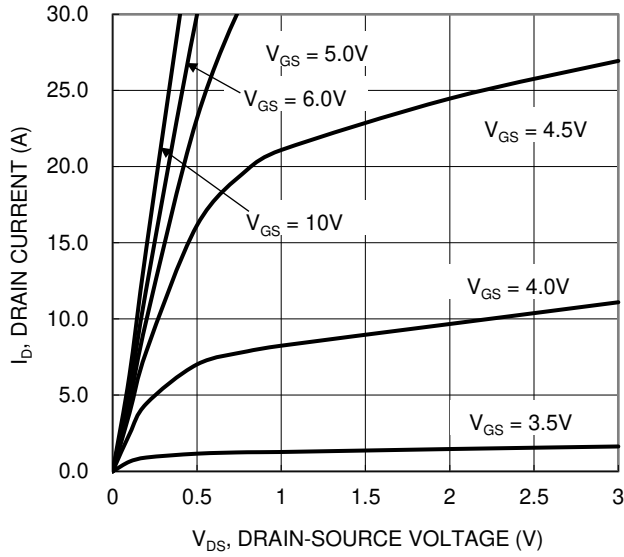


Figure 1. Typical Output Characteristic

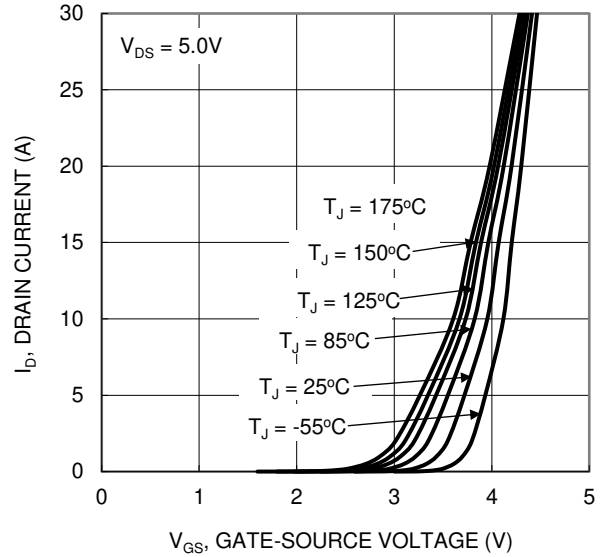


Figure 2. Typical Transfer Characteristic

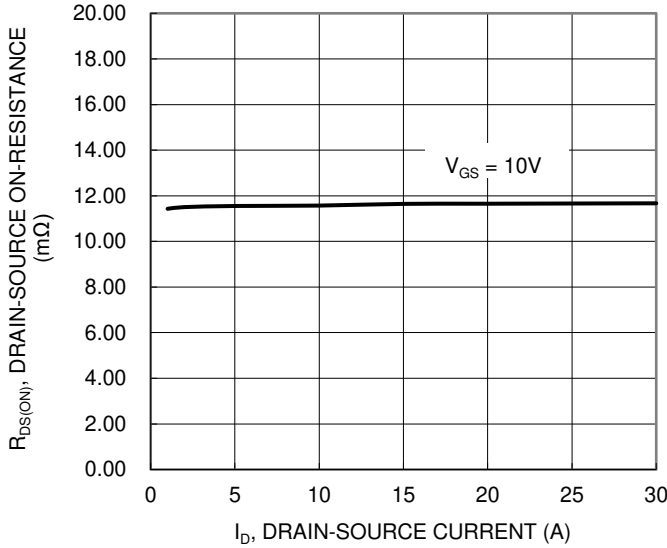


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

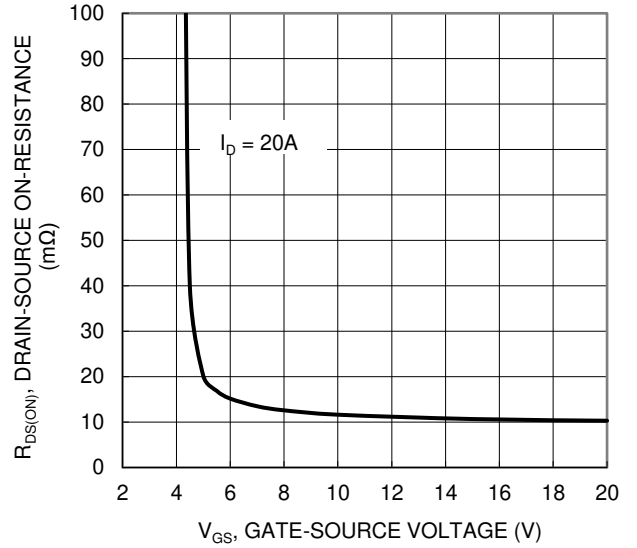


Figure 4. Typical Transfer Characteristic

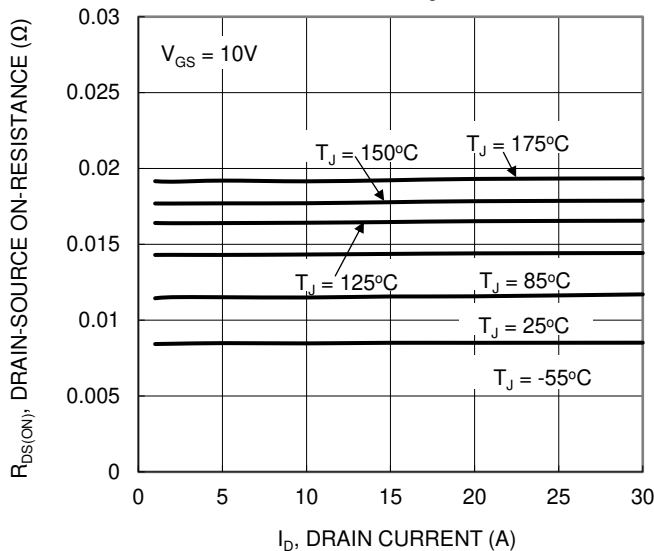


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

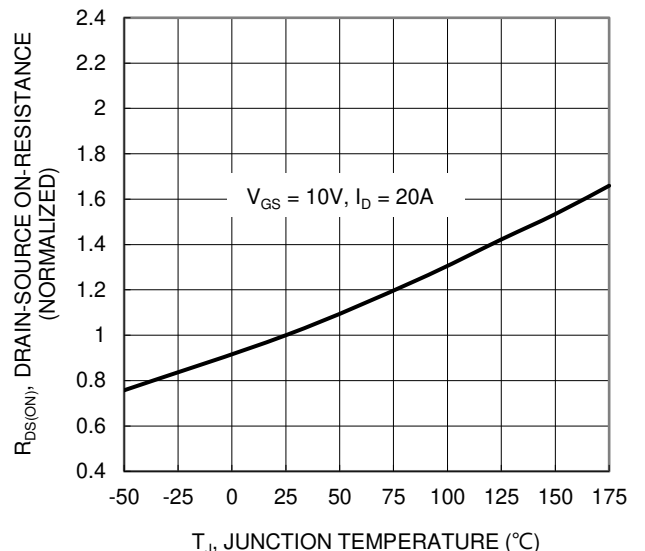
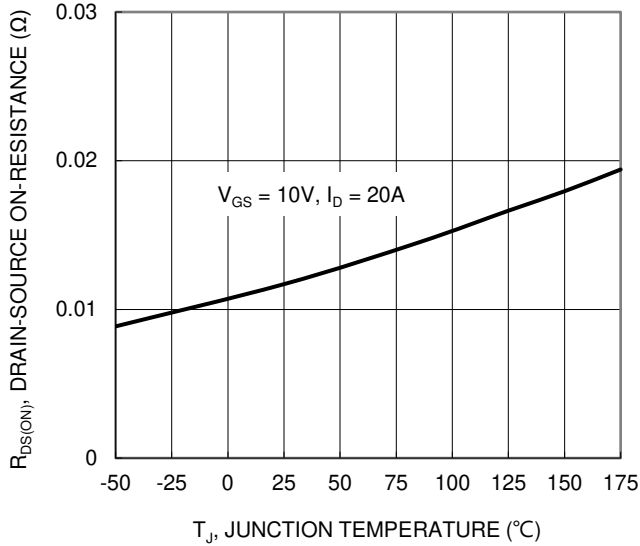
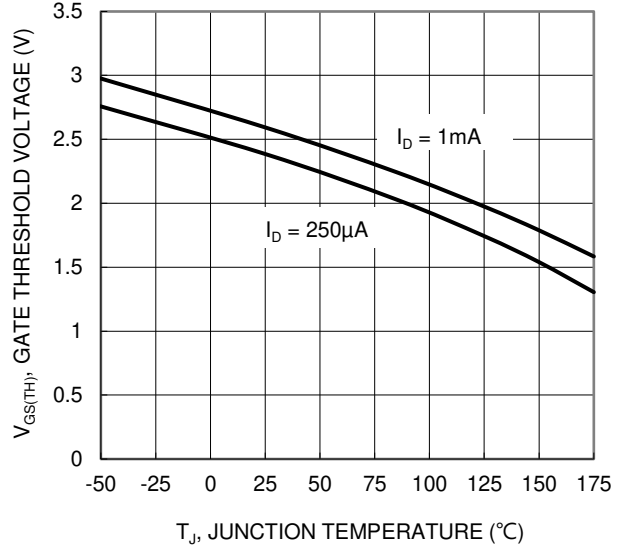


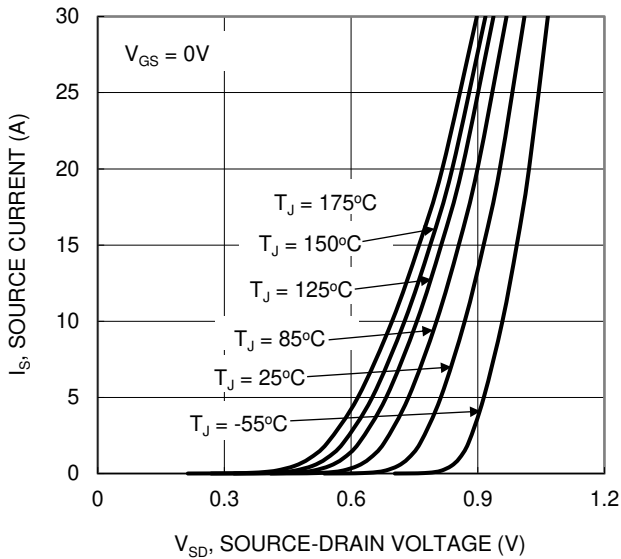
Figure 6. On-Resistance Variation with Temperature



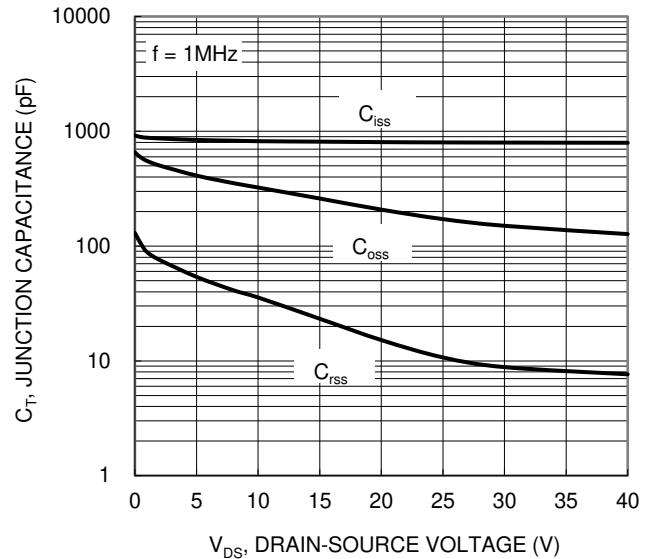
T<sub>J</sub>, JUNCTION TEMPERATURE (°C)  
Figure 7. On-Resistance Variation with Temperature



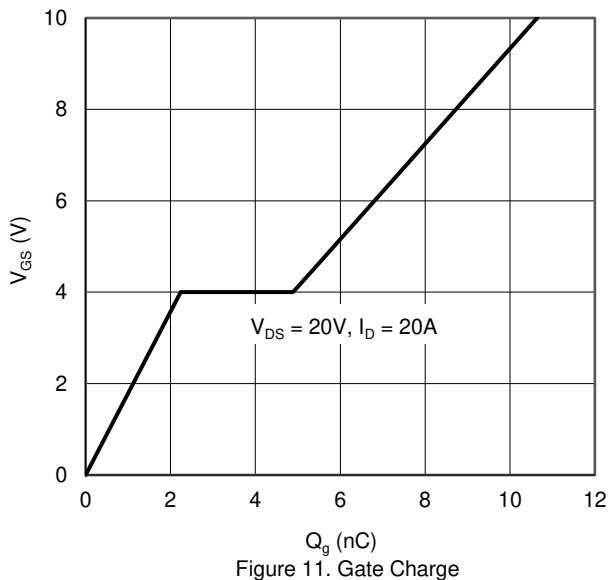
T<sub>J</sub>, JUNCTION TEMPERATURE (°C)  
Figure 8. Gate Threshold Variation vs. Temperature



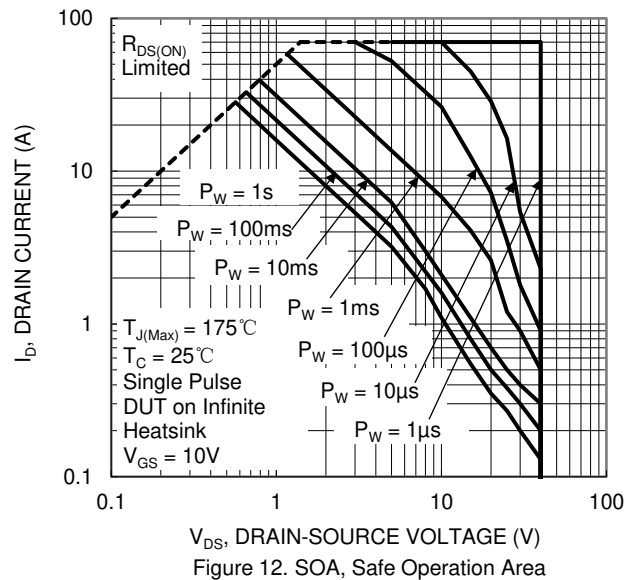
V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V)  
Figure 9. Diode Forward Voltage vs. Current



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)  
Figure 10. Typical Junction Capacitance



Q<sub>g</sub> (nC)  
Figure 11. Gate Charge



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)  
Figure 12. SOA, Safe Operation Area

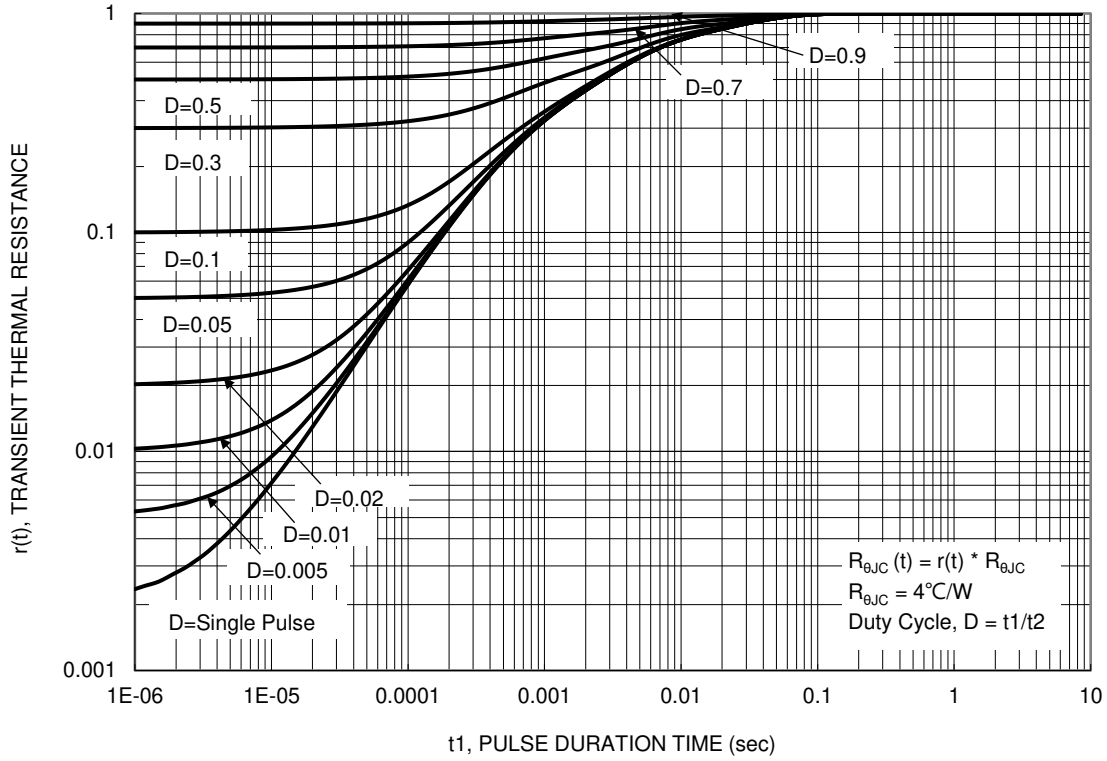


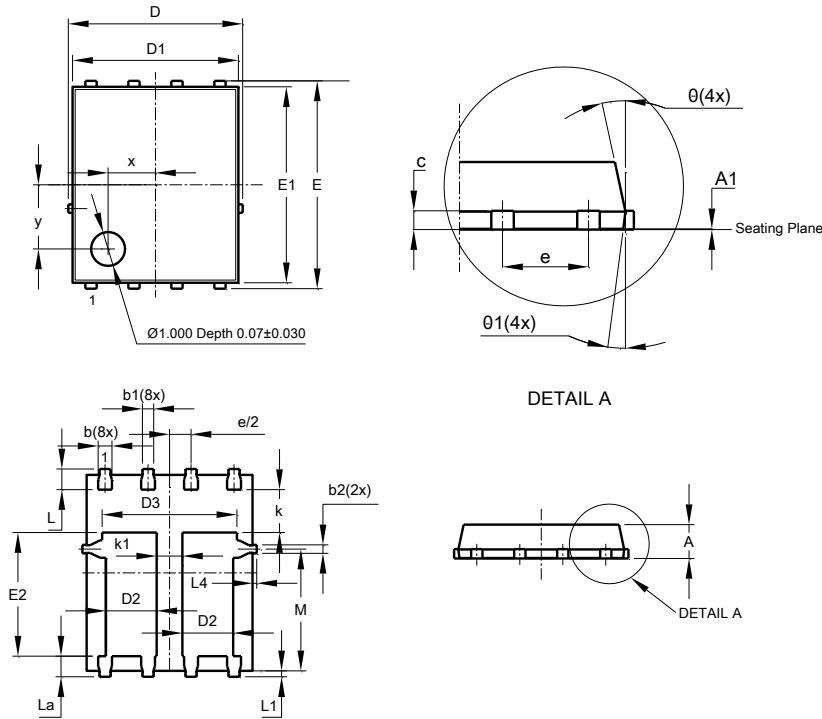
Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

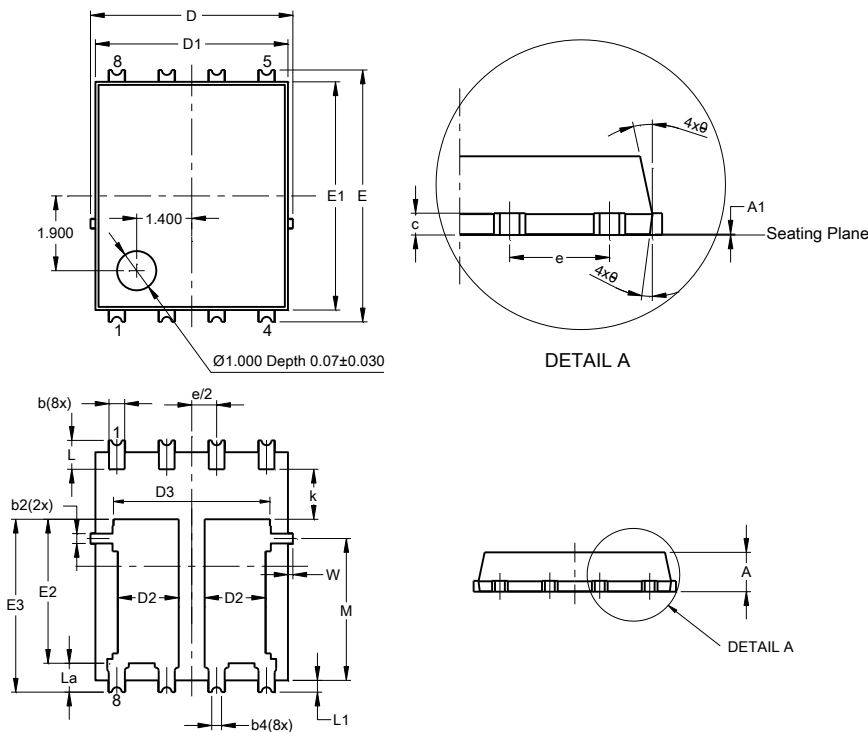
**PowerDI5060-8 (Type C)**



PowerDI5060-8 (Type C)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	1.40	1.60	1.50
D3	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.76	3.66
e	1.27BSC		
k	-	-	1.27
k1	0.56	-	-
L	0.51	0.71	0.61
La	0.51	0.71	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Site 2:

**PowerDI5060-8/SWP (Type UXD)**



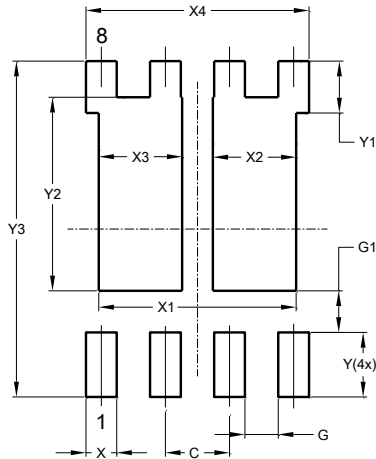
PowerDI5060-8/SWP (Type UXD)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	1.46	1.66	1.55
D3	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
M	3.205	4.005	3.605
W	0.025	0.225	0.125
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

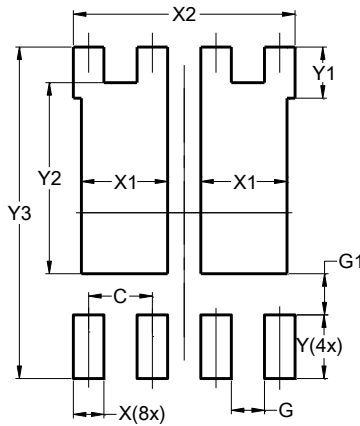
**PowerDI5060-8 (Type C)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	1.650
X3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

Site 2:

**PowerDI5060-8/SWP (Type UXD)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	1.720
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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